

recited in claim 3, characterized in that said window is formed from a group composed of at least two micro-apertures.

[5] The Group III nitride semiconductor crystal manufacturing method recited in claim 1, characterized in that said step of growing at least one said Group III nitride semiconductor crystal includes:

a step of disposing at least one seed crystal on said starting substrate; and

a step of growing said Group III nitride semiconductor crystal with said seed crystal as its nucleus.

[6] The Group III nitride semiconductor crystal manufacturing method recited in any one of claims 1 to 5, characterized in that whichever of an etching, lasing, or cleaving method is used in said step of separating from said starting substrate said Group III nitride semiconductor crystal.

[7] The Group III nitride semiconductor crystal manufacturing method recited in any one of claims 1 to 6, characterized in that the conformation of said Group III nitride semiconductor crystal is hexagonal-platelike, rectangular-platelike, or triangular-platelike.

[8] (Amended) The Group III nitride semiconductor crystal manufacturing method recited in any one of claims 1 to 7, characterized in that said Group III nitride semiconductor crystal is grown at a rate of at least 10  $\mu\text{m/hr}$  but not more than 300  $\mu\text{m/hr}$ .

[9] The Group III nitride semiconductor crystal manufacturing method recited in any one of claims 1 to 7, characterized in that said Group III nitride

an etching, lasing, or cleaving method is used in said step of separating from said starting substrate said Group III nitride semiconductor crystal constituted by said Group III nitride semiconductor crystal substrate and said Group III nitride semiconductor crystal layer.

[18] The method of manufacturing a Group III nitride semiconductor device recited in any one of claims 12 to 17, characterized in that the conformation of said Group III nitride semiconductor crystal substrate and said Group III nitride semiconductor crystal layer is hexagonal-platelike, rectangular-platelike, or triangular-platelike.

[19] (Amended) The method of manufacturing a Group III nitride semiconductor device recited in any one of claims 12 to 18, characterized in that said Group III nitride semiconductor crystal substrate is grown at a rate of at least 10  $\mu\text{m/hr}$  but not more than 300  $\mu\text{m/hr}$ .

[20] The method of manufacturing a Group III nitride semiconductor device recited in any one of claims 12 to 18, characterized in that said Group III nitride crystal substrate has an impurity concentration that is not more than  $5 \times 10^{19} \text{ cm}^{-3}$ .

[21] The method of manufacturing a Group III nitride semiconductor device recited in any one of claims 12 to 18, characterized in that an off angle between the principal face of said Group III nitride crystal substrate and whichever of its (0001) face, ( $1\bar{1}00$ ) face, ( $11\bar{2}0$ ) face, ( $1\bar{1}01$ ) face, ( $1\bar{1}02$ ) face, ( $11\bar{2}1$ ) face, or ( $11\bar{2}2$ ) face is  $0^\circ$  or more but not more than  $4^\circ$ .

[22] A Group III nitride semiconductor device manufactured using a